

# 2N6394 Series

Preferred Device

## Silicon Controlled Rectifiers

### Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls and power supplies.

- Glass Passivated Junctions with Center Gate Geometry for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Blocking Voltage to 800 Volts
- Device Marking: Logo, Device Type, e.g., 2N6394, Date Code

**\*MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1.) ( $T_J = -40$ to $125^\circ\text{C}$ , Sine Wave, 50 to 60 Hz, Gate Open)	$V_{\text{DRM}}$ , $V_{\text{RRM}}$		Volts
2N6394		50	
2N6395		100	
2N6397		400	
2N6399		800	
On-State RMS Current ( $180^\circ$ Conduction Angles; $T_C = 90^\circ\text{C}$ )	$I_{\text{T(RMS)}}$	12	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, $T_J = 90^\circ\text{C}$ )	$I_{\text{TSM}}$	100	A
Circuit Fusing ( $t = 8.3$ ms)	$I^2t$	40	$\text{A}^2\text{s}$
Forward Peak Gate Power (Pulse Width $\leq 1.0$ $\mu\text{s}$ , $T_C = 90^\circ\text{C}$ )	$P_{\text{GM}}$	20	Watts
Forward Average Gate Power ( $t = 8.3$ ms, $T_C = 90^\circ\text{C}$ )	$P_{\text{G(AV)}}$	0.5	Watts
Forward Peak Gate Current (Pulse Width $\leq 1.0$ $\mu\text{s}$ , $T_C = 90^\circ\text{C}$ )	$I_{\text{GM}}$	2.0	A
Operating Junction Temperature Range	$T_J$	$-40$ to $+125$	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{stg}}$	$-40$ to $+150$	$^\circ\text{C}$

\*Indicates JEDEC Registered Data

1.  $V_{\text{DRM}}$  and  $V_{\text{RRM}}$  for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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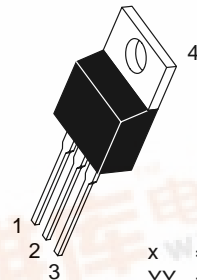
SCRs

12 AMPERES RMS

50 thru 800 VOLTS

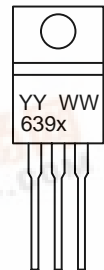


MARKING  
DIAGRAM



TO-220AB  
CASE 221A  
STYLE 3

x = 4, 5, 7 or 9  
YY = Year  
WW = Work Week



#### PIN ASSIGNMENT

1	Cathode
2	Anode
3	Gate
4	Anode

#### ORDERING INFORMATION

Device	Package	Shipping
2N6394	TO220AB	500/Box
2N6395	TO220AB	500/Box
2N6397	TO220AB	500/Box
2N6399	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.



## 2N6394 Series

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	$T_L$	260	°C

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

*Peak Repetitive Forward or Reverse Blocking Current ( $V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}$ , Gate Open) $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	$I_{DRM}, I_{RRM}$	–	–	10	$\mu\text{A}$
		–	–	2.0	mA

### ON CHARACTERISTICS

*Peak Forward On-State Voltage (Note 2.) ( $I_{TM} = 24 \text{ A Peak}$ )	$V_{TM}$	–	1.7	2.2	Volts
*Gate Trigger Current (Continuous dc) ( $V_D = 12 \text{ Vdc}$ , $R_L = 100 \text{ Ohms}$ )	$I_{GT}$	–	5.0	30	mA
*Gate Trigger Voltage (Continuous dc) ( $V_D = 12 \text{ Vdc}$ , $R_L = 100 \text{ Ohms}$ )	$V_{GT}$	–	0.7	1.5	Volts
Gate Non-Trigger Voltage ( $V_D = 12 \text{ Vdc}$ , $R_L = 100 \text{ Ohms}$ , $T_J = 125^\circ\text{C}$ )	$V_{GD}$	0.2	–	–	Volts
*Holding Current ( $V_D = 12 \text{ Vdc}$ , Initiating Current = 200 mA, Gate Open)	$I_H$	–	6.0	50	mA
Turn-On Time ( $I_{TM} = 12 \text{ A}$ , $I_{GT} = 40 \text{ mAdc}$ , $V_D = \text{Rated } V_{DRM}$ )	$t_{gt}$	–	1.0	2.0	$\mu\text{s}$
Turn-Off Time ( $V_D = \text{Rated } V_{DRM}$ ) ( $I_{TM} = 12 \text{ A}$ , $I_R = 12 \text{ A}$ ) ( $I_{TM} = 12 \text{ A}$ , $I_R = 12 \text{ A}$ , $T_J = 125^\circ\text{C}$ )	$t_q$	–	15	–	$\mu\text{s}$
		–	35	–	

### DYNAMIC CHARACTERISTICS

Critical Rate-of-Rise of Off-State Voltage Exponential ( $V_D = \text{Rated } V_{DRM}$ , $T_J = 125^\circ\text{C}$ )	$dv/dt$	–	50	–	V/ $\mu\text{s}$
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\*Indicates JEDEC Registered Data

2. Pulse Test: Pulse Width  $\leq 300 \mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .

## 2N6394 Series

### Voltage Current Characteristic of SCR

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Off State Reverse Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Peak On State Voltage
$I_H$	Holding Current

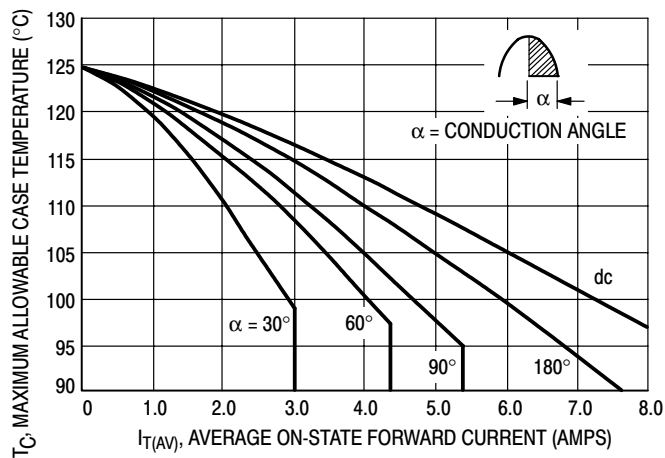
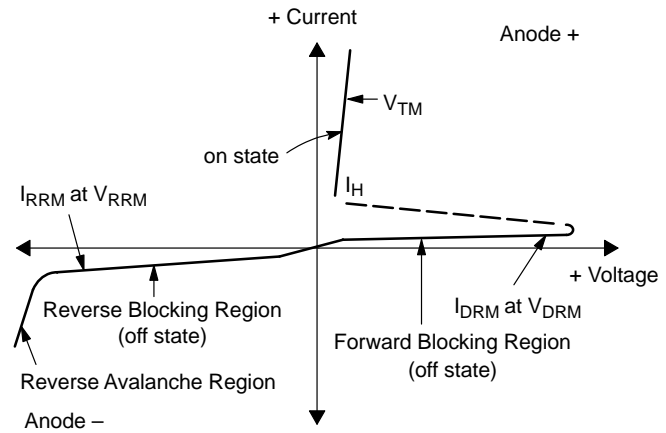


Figure 1. Current Derating

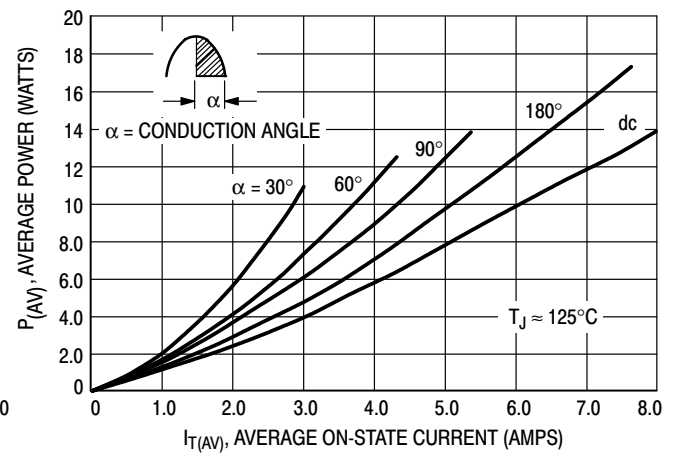


Figure 2. Maximum On-State Power Dissipation

## 2N6394 Series

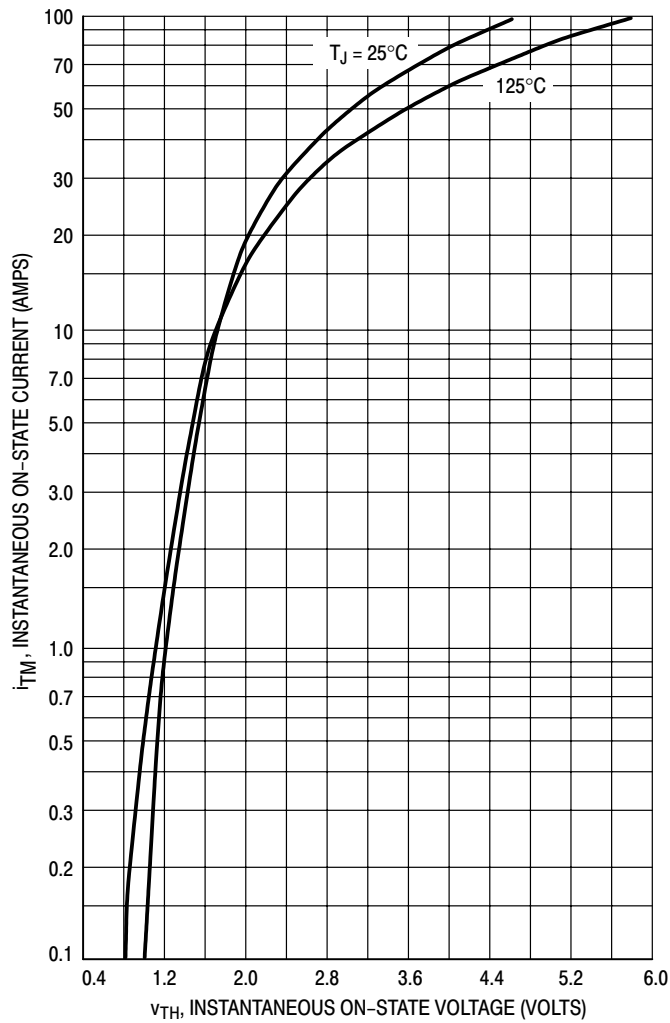


Figure 3. On-State Characteristics

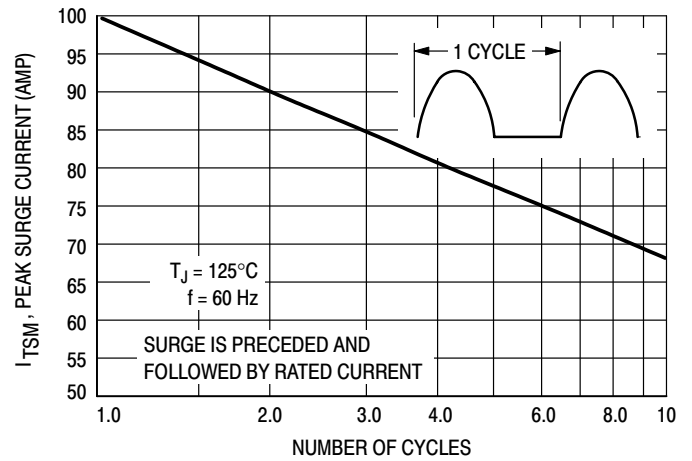


Figure 4. Maximum Non-Repetitive Surge Current

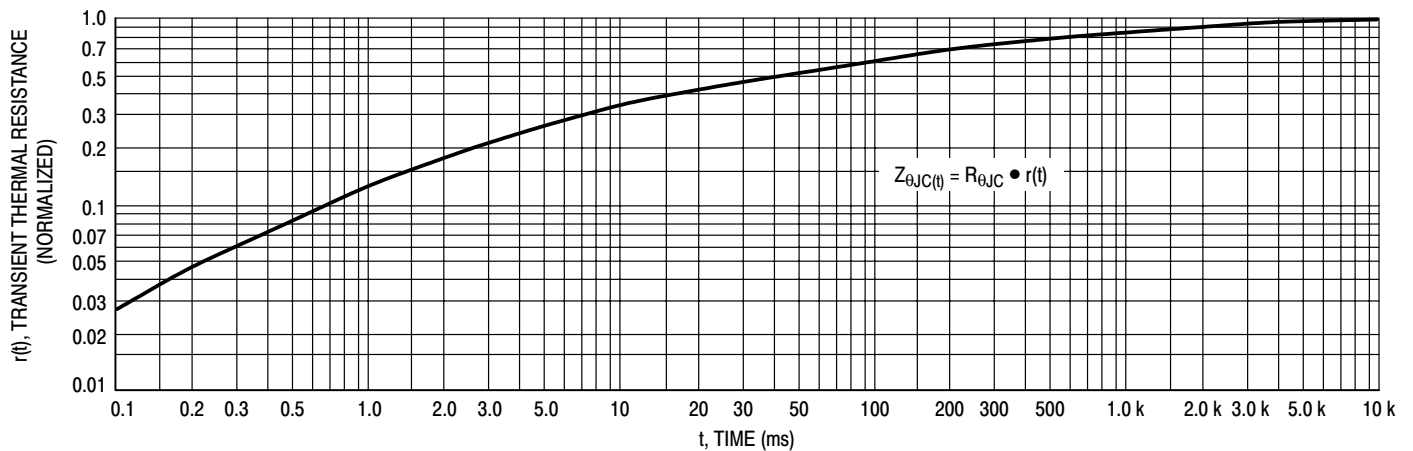


Figure 5. Thermal Response

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### TYPICAL CHARACTERISTICS

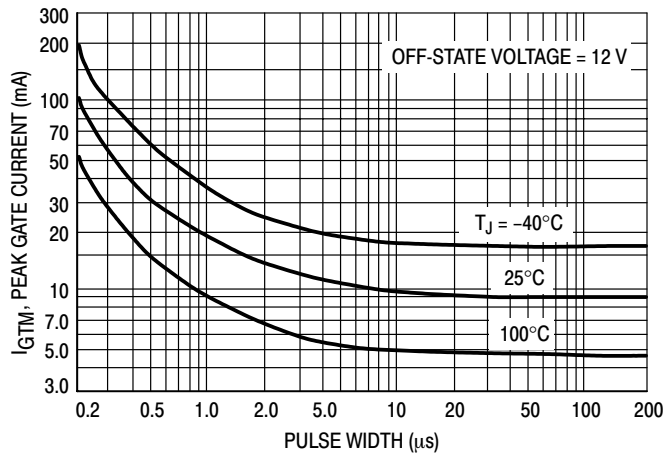


Figure 6. Typical Gate Trigger Current versus Pulse Width

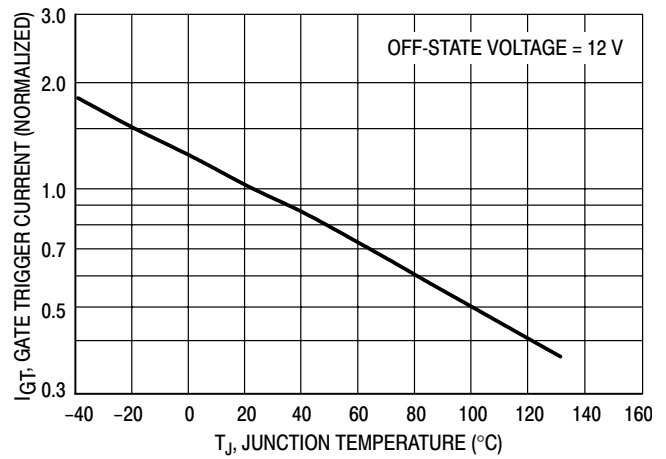


Figure 7. Typical Gate Trigger Current versus Temperature

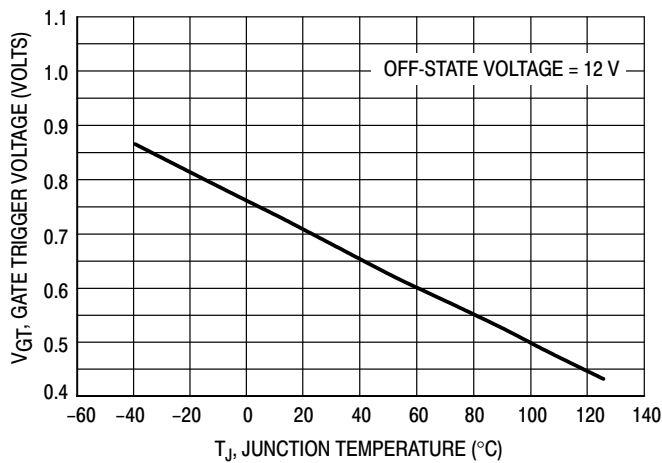


Figure 8. Typical Gate Trigger Voltage versus Temperature

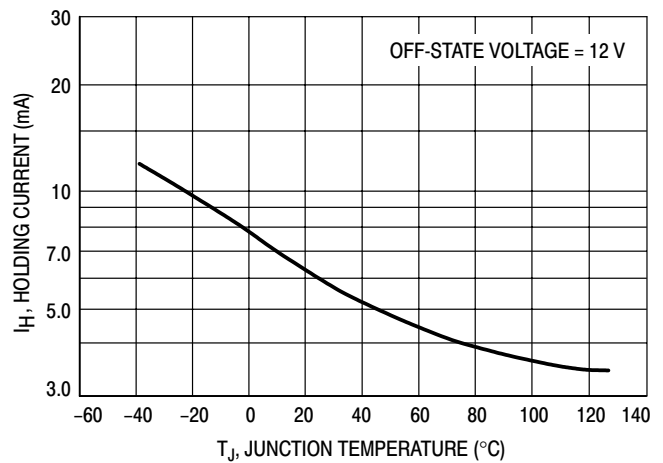
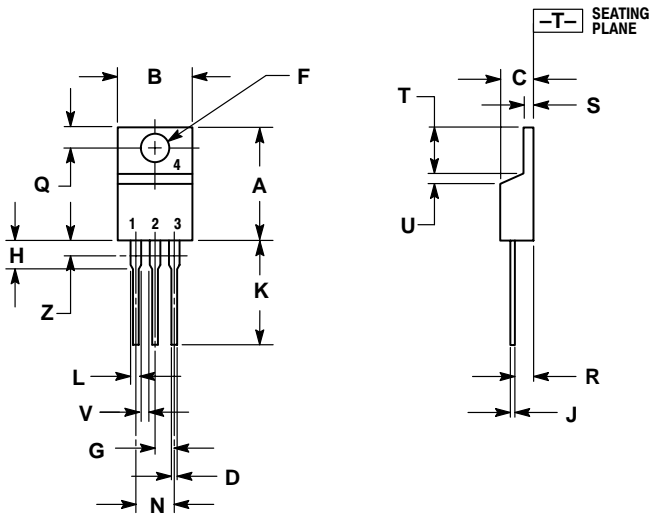


Figure 9. Typical Holding Current versus Temperature

# 2N6394 Series

## PACKAGE DIMENSIONS

TO-220AB  
CASE 221A-07  
ISSUE AA



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04


### STYLE 3:

- PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE

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### Notes

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